



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
PNP SILICON Transistor**

VOLTAGE 80 Volts CURRENT 1 Ampere

CHT4033XGF

APPLICATION

- * Telephony and professional communication equipment.
- * Other switching applications.

FEATURE

- * Small flat package. (SC-62/SOT-89)
- * Suitable for high packing density.
- * High saturation current capability.
- * Voltage controlled small signal switch.

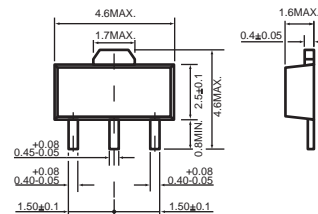
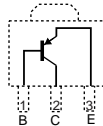
CONSTRUCTION

- * PNP SILICON Transistor



SC-62/SOT-89

CIRCUIT



- 1 Base
- 2 Collector (Heat Sink)
- 3 Emitter

Dimensions in millimeters

SC-62/SOT-89

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	—	80	V
V _{CEO}	collector-emitter voltage	open base	—	80	V
V _{EBO}	emitter-base voltage	open collector	—	5.0	V
I _C	collector current (DC)		—	1.0	A
I _{CM}	peak collector current		—	1.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	—	1.2	W
T _{stg}	storage temperature		−65	+150	°C
T _j	junction temperature		—	150	°C
T _{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT4033XGP)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	357	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 1.0\text{ A}; V_{CE} = 5\text{ V}$	75 100 70 25	– 300 – –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	0.15	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	0.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	0.9	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	1.1	V
C_{ob}	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	20	pF
C_{ib}	emitter capacitance	$I_C = I_C = 0; V_{BE} = 500\text{ mV}; f = 1\text{ MHz}$	–	110	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 1.0\text{ MHz}$	100	–	MHz